



# STN3N45K3 STQ3N45K3-AP, STU3N45K3

N-channel 450 V, 3.2  $\Omega$ , 1.8 A, TO-92, SOT-223, IPAK  
SuperMESH3™ Power MOSFET

Preliminary data

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>	P <sub>w</sub>
STN3N45K3	450 V	< 3.8 $\Omega$	0.6 A	2 W
STQ3N45K3-AP	450 V	< 3.8 $\Omega$	0.6 A	2.5 W
STU3N45K3	450 V	< 3.8 $\Omega$	1.8 A	27 W

- 100% avalanche tested
- Extremely high dv/dt capability
- Gate charge minimized
- Very low intrinsic capacitance
- Improved diode reverse recovery characteristics
- Zener-protected

## Application

- Switching applications

## Description

The new SuperMESH3™ series is obtained through the combination of a further fine tuning of ST's well established strip-based PowerMESH™ layout with a new optimization of the vertical structure. In addition to reducing on-resistance significantly versus previous generation, special attention has been taken to ensure a very good dv/dt capability and higher margin in breakdown voltage for the most demanding application.

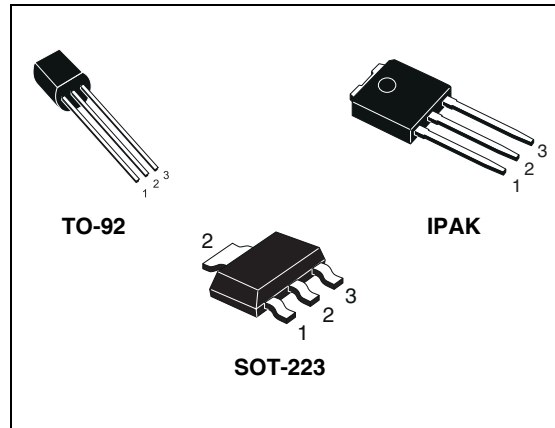


Figure 1. Internal schematic diagram

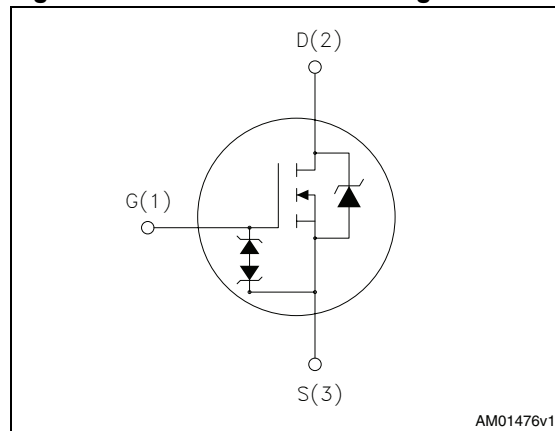


Table 1. Device summary

Order codes	Marking	Package	Packaging
STN3N45K3	3N45K3	SOT-223	Tube
STQ3N45K3-AP	3N45K3	TO-92	Ammopak
STU3N45K3	3N45K3	IPAK	Tube

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value			Unit
		SOT-223	TO-92	IPAK	
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	450			V
$V_{GS}$	Gate- source voltage	$\pm 30$			V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	0.6		1.8	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	0.38		1	A
$I_{DM}^{(1)}$	Drain current (pulsed)	2.4		7.2	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	2	2.5	27	W
$T_{stg}$	Storage temperature	-55 to 150			$^\circ\text{C}$
$T_j$	Max. operating junction temperature	150			$^\circ\text{C}$

1. Pulse width limited by safe operating area.

**Table 3. Thermal data**

Symbol	Parameter	SOT-223	TO-92	IPAK	Unit
$R_{thj-case}$	Thermal resistance junction-case max	62.50	50	4.63	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max			100	$^\circ\text{C}/\text{W}$
$T_I$	Maximum lead temperature for soldering purpose	300			$^\circ\text{C}$

**Table 4. Avalanche characteristics**

Symbol	Parameter	Max value	Unit
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ max)	0.5	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{V}$ )	TBD	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 5. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	450			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$ , $T_C = 125\text{ °C}$			1 50	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 50\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 0.5\text{ A}$		3.2	3.8	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	150	-	pF
$C_{oss}$	Output capacitance			30		pF
$C_{rss}$	Reverse transfer capacitance			6		pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	TBD	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 360\text{ V}$ , $I_D = 1.8\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 3</a> )	-	6	-	nC
$Q_{gs}$	Gate-source charge			TBD		nC
$Q_{gd}$	Gate-drain charge			TBD		nC

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 225\text{ V}$ , $I_D = 0.5\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 2</a> )	-	TBD	-	ns
$t_r$	Rise time			TBD		ns
$t_{d(off)}$	Turn-off-delay time			TBD		ns
$t_f$	Fall time			TBD		ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		1.8	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		7.2	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 1.8 \text{ A}, V_{GS} = 0$	-		TBD	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 1.8 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 100 \text{ V}$ (see <a href="#">Figure 7</a> )	-	TBD		ns
$Q_{rr}$	Reverse recovery charge					
$I_{RRM}$	Reverse recovery current					
$t_{rr}$	Reverse recovery time	$I_{SD} = 1.8 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 100 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 7</a> )	-	TBD		ns
$Q_{rr}$	Reverse recovery charge					
$I_{RRM}$	Reverse recovery current					

1. Pulse width limited by safe operating area.

2. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

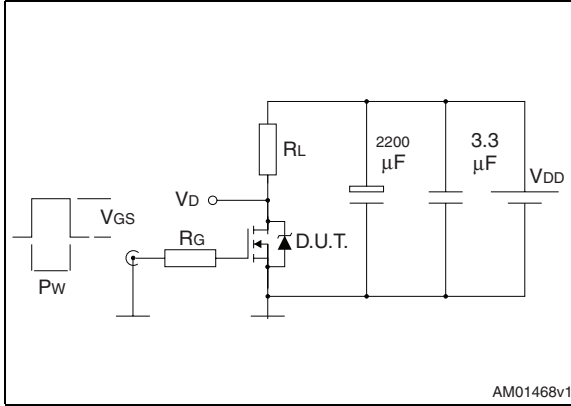
**Table 9. Gate-source Zener diode**

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$BV_{GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1 \text{ mA}$ (open drain)	30	-		V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

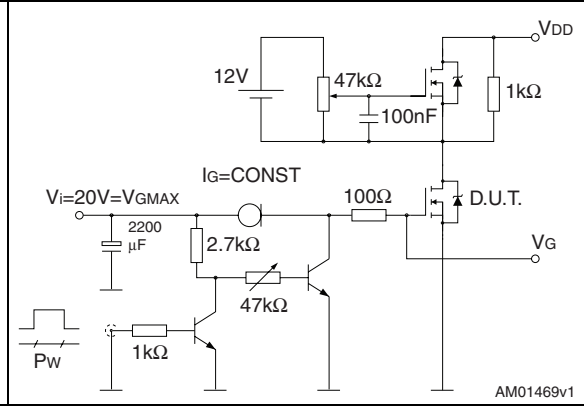
### 3 Test circuits

**Figure 2. Switching times test circuit for resistive load**



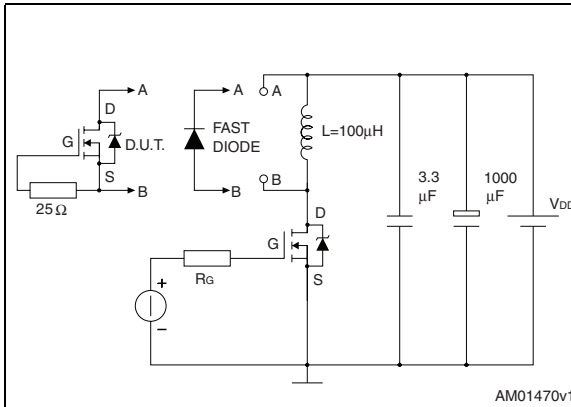
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**Figure 3. Gate charge test circuit**



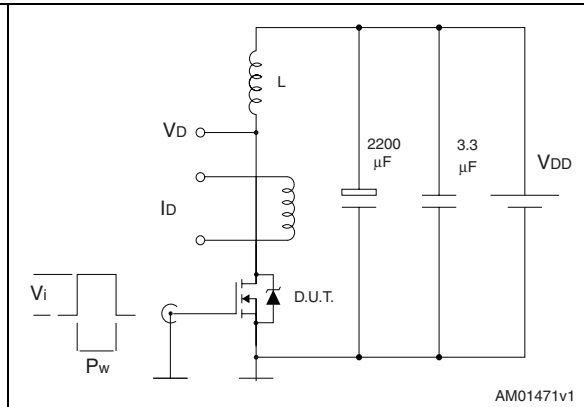
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**Figure 4. Test circuit for inductive load switching and diode recovery times**



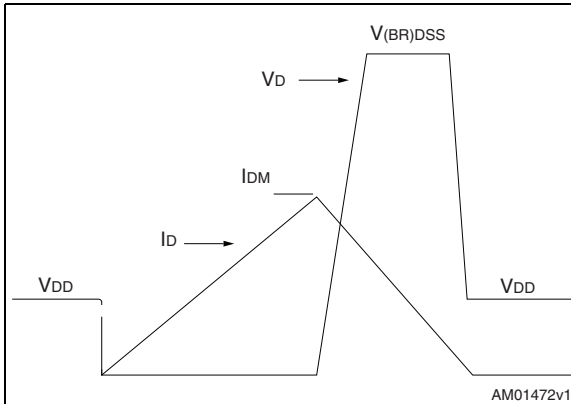
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**Figure 5. Unclamped Inductive load test circuit**



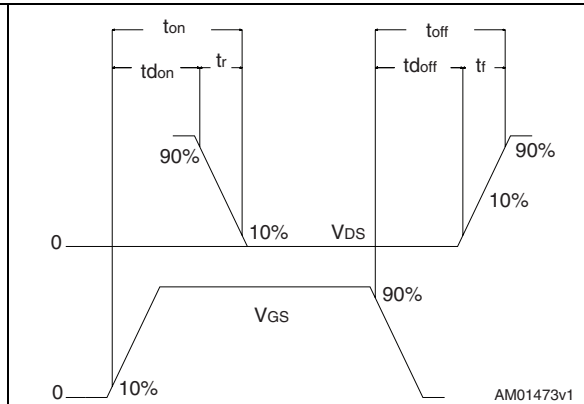
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**Figure 6. Unclamped inductive waveform**



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**Figure 7. Switching time waveform**



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## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

SOT-223 mechanical data			
DIM.	mm.		
	min.	typ	max.
A			1.80
A1	0.02		0.1
B	0.60	0.70	0.85
B1	2.90	3.00	3.15
c	0.24	0.26	0.35
D	6.30	6.50	6.70
e		2.30	
e1		4.60	
E	3.30	3.50	3.70
H	6.70	7.00	7.30
V			10 °

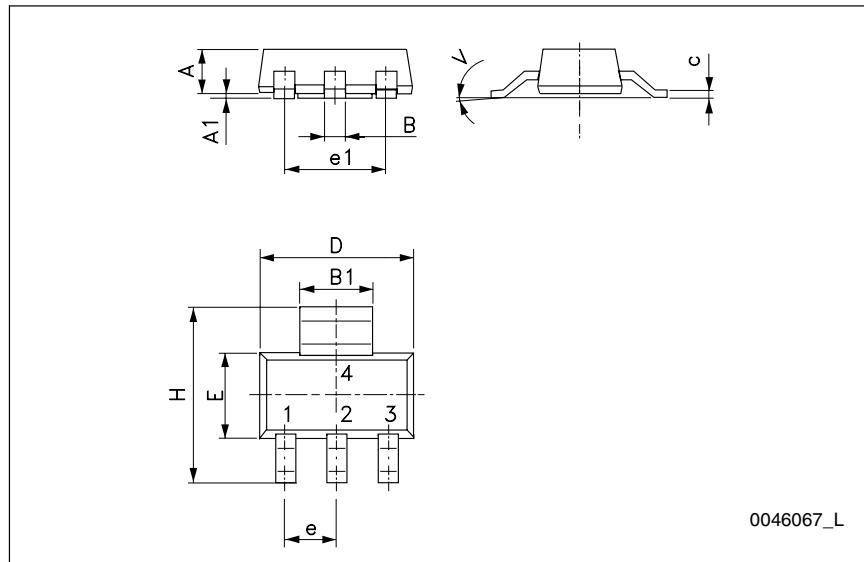
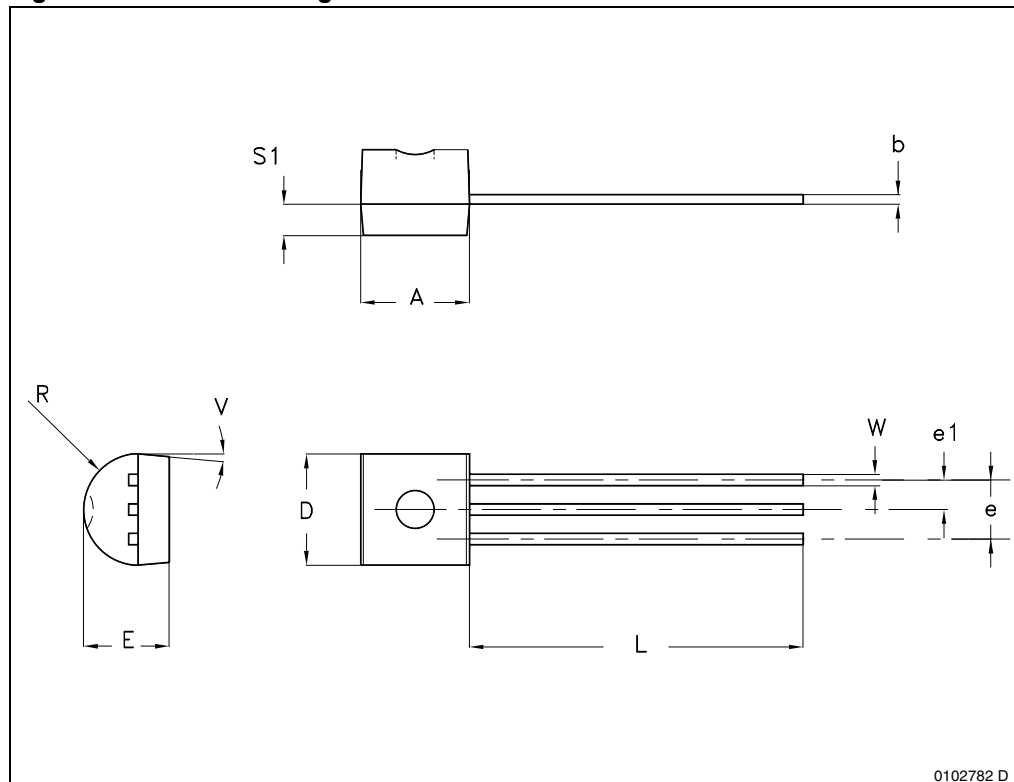




Table 10. TO-92 mechanical data

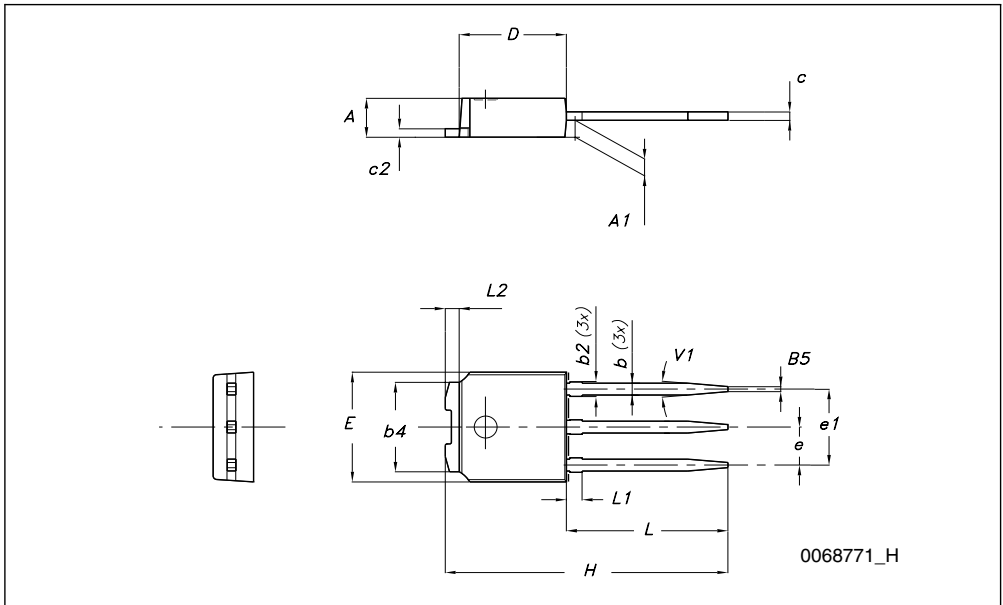
Dim.	mm		
	Min.	Typ.	Max.
A	4.32		4.95
b	0.36		0.51
D	4.45		4.95
E	3.30		3.94
e	2.41		2.67
e1	1.14		1.40
L	12.70		15.49
R	2.16		2.41
S1	0.92		1.52
W	0.41		0.56
V		5°	

Figure 8. TO-92 drawing



**TO-251 (IPAK) mechanical data**

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



## 5 Revision history

Table 11. Document revision history

Date	Revision	Changes
02-Mar-2010	1	First release
23-Apr-2010	2	Changed root part number

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